Annealing process for annealing a structure

ABSTRACT

The invention relates to a process for annealing a structure comprising at least one wafer, the annealing process comprising a first step for annealing the structure in an oxidizing atmosphere so as to form an oxide layer (310) on at least part of its exposed surface, the structure being in contact with a holder (312) in a first position. The process furthermore comprises a step of shifting the structure on the holder into a second position in which the region or regions (314) of contact between the structure and the holder during the first annealing step are exposed, and a second annealing step for annealing the structure in the second position in an oxidizing atmosphere.

Fig. 3C